

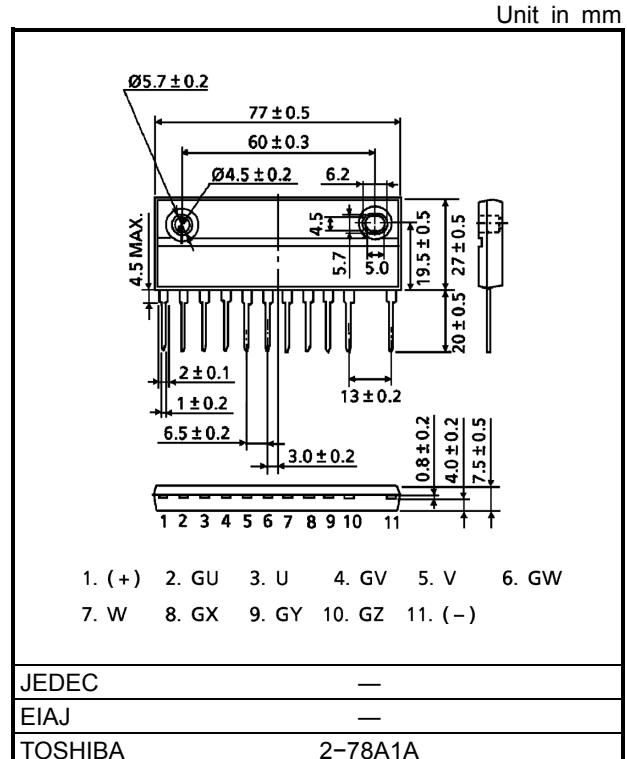
TOSHIBA GTR Module Silicon N Channel IGBT

MP6752

High Power Switching Applications

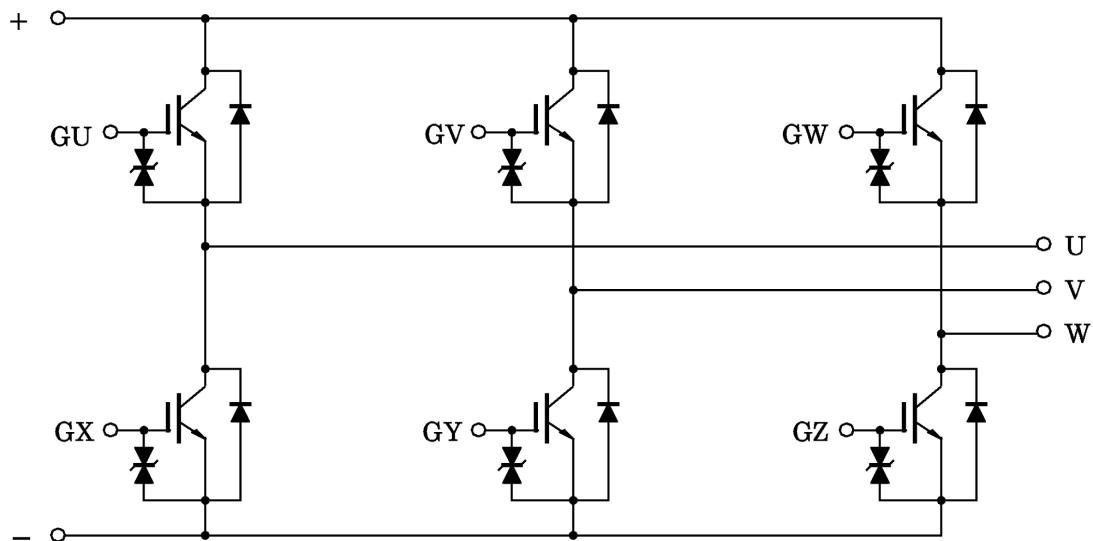
Motor Control Applications

- The electrodes are isolated from case.
- 6 IGBTs are built into 1 package.
- Enhancement-mode
- Low saturation voltage
: $V_{CE(sat)} = 4.0V$ (max.) ($I_C = 20A$)
- High speed: $t_f = 0.35\mu s$ (max.) ($I_C = 20A$)
 $t_{rr} = 0.15\mu s$ (max.) ($I_F = 20A$)



Weight: 44g

Equivalent Circuit



Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	600	V
Gate-emitter voltage		V_{GES}	± 20	V
Collector current	DC	I_C	20	A
	1ms	I_{CP}	40	
Forward current	DC	I_F	20	A
	1ms	I_{FM}	40	
Collector power dissipation ($T_c = 25^\circ\text{C}$)		P_C	60	W
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-40~125	$^\circ\text{C}$
Isolation voltage		V_{Isol}	2500 (AC 1 minute)	V
Screw torque		—	1.5	N·m

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Gate leakage current	I_{GES}	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$	—	—	± 20	μA
Collector cut-off current	I_{CES}	$V_{CE} = 600\text{V}$, $V_{GE} = 0$	—	—	1.0	mA
Gate-emitter cut-off voltage	$V_{GE(\text{off})}$	$I_C = 20\text{mA}$, $V_{CE} = 5\text{V}$	3.0	—	6.0	V
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 20\text{A}$, $V_{GE} = 15\text{V}$	—	3.0	4.0	V
Input capacitance	C_{ies}	$V_{CE} = 10\text{V}$, $V_{GE} = 0$, $f = 1\text{MHz}$	—	1300	—	pF
Switching time	Rise time	t_r		—	0.3	0.6
	Turn-on time	t_{on}		—	0.4	0.8
	Fall time	t_f		—	0.2	0.35
	Turn-off time	t_{off}		—	0.5	1.0
Forward voltage	V_F	$I_F = 20\text{A}$, $V_{GE} = 0$	—	1.7	2.5	V
Reverse recovery time	t_{rr}	$I_F = 20\text{A}$, $V_{GE} = -10\text{V}$ $di/dt = 50\text{A}/\mu\text{s}$	—	0.08	0.15	μs
Thermal resistance	$R_{th(j-c)}$	Transistor	—	—	2.08	$^\circ\text{C}/\text{W}$
		Diode	—	—	3.09	